

Features

- Efficiency up to 96%
- Only 40µA (Typ. per Channel) Quiescent Current
- Output Current: Up to 1A per Channel
- Internal Synchronous Rectifier
- 1.5MHz Switching Frequency
- Soft Start
- Under-Voltage Lockout
- Short Circuit Protection
- Thermal Shutdown
- Small 12L WDFN3x3 Package
- Pb-Free Package and RoHS Compliant

Applications

- Cellular Phone
- Portable Electronics
- Personal Information Appliances
- Wireless and DSL Modems
- MP3 Players

General Description

The PAM2306 is a dual step-down current-mode, DC-DC converter. At heavy load, the constant-frequency PWM control performs excellent stability and transient response. To ensure the longest battery life in portable applications, the PAM2306 provides a power-saving Pulse-Skipping Modulation (PSM) mode to reduce quiescent current under light load operation.

The PAM2306 supports a range of input voltages from 2.5V to 5.5V, allowing the use of a single Li+/Li-polymer cell, multiple Alkaline/NiMH cell, USB, and other standard power sources. The dual output voltages are available for 3.3V, 2.8V, 2.5V, 1.8V, 1.5V, 1.2V or adjustable. All versions employ internal power switch and synchronous rectifier for to minimize external part count and realize high efficiency. During shutdown, the input is disconnected from the output and the shutdown current is less than 0.1µA. Other key features include under-voltage lockout to prevent deep battery discharge.

Typical Application

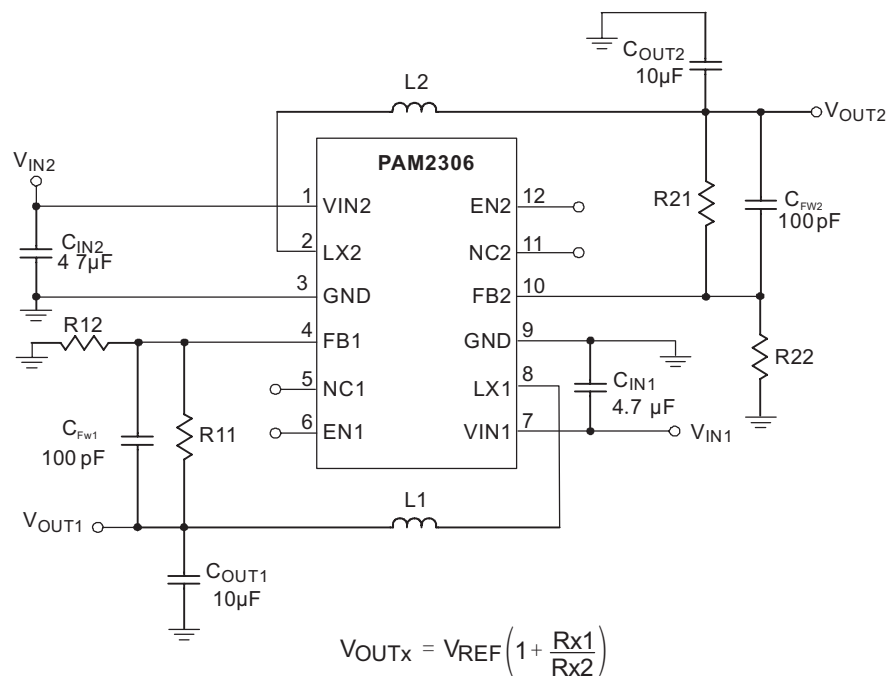


Figure 1. Adjustable Voltage Regulator

Typical Application

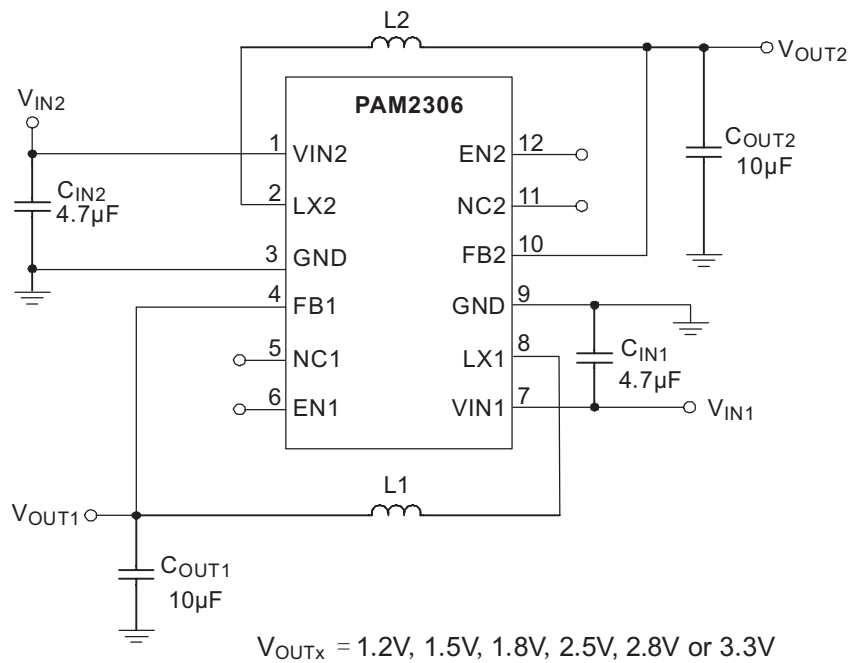
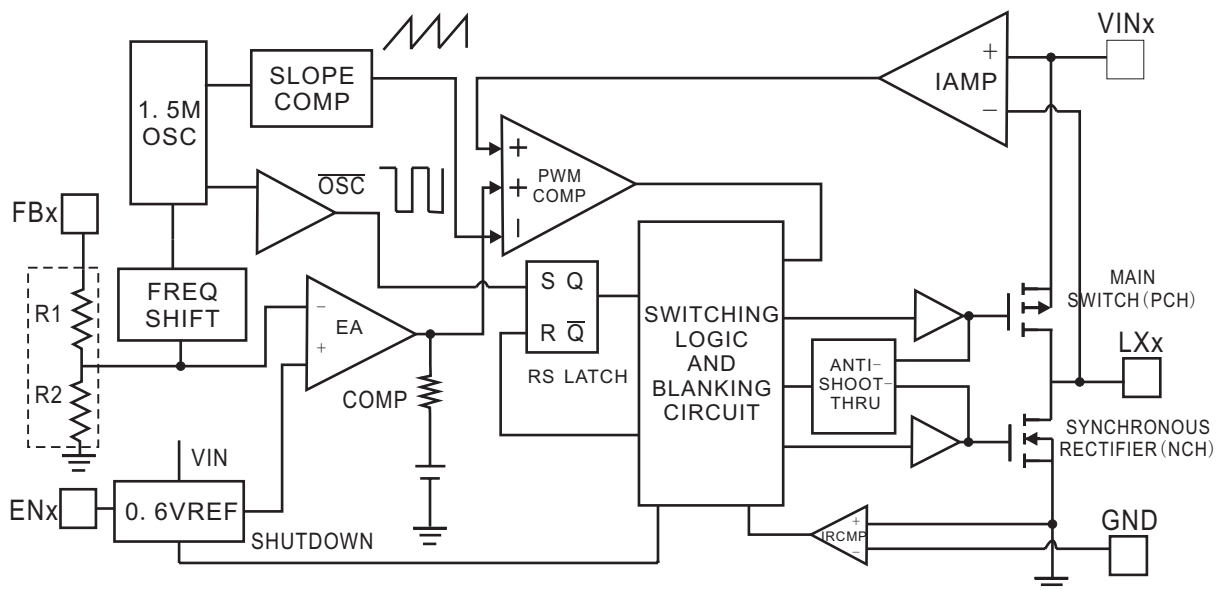
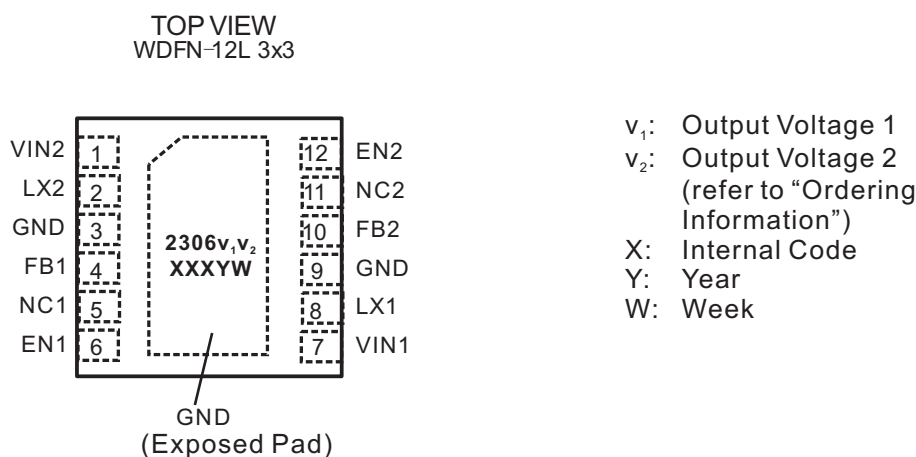


Figure 2. Fixed Voltage Regulator

Block Diagram



Pin Configuration and Marking Information



| Pin No. | Pin Name | Pin Function |
|----------------------|----------|---|
| 1 | VIN2 | Power Input of Channel 2. |
| 2 | LX2 | Pin for Switching of Channel 2. |
| 3, 9, Exposed Pad | GND | Ground. The exposed pad must be soldered to a large PCB and connected to GND for maximum power dissipation. |
| 4 | FB1 | Feedback of Channel 1. |
| 5, 11 | NC1, NC2 | No Connection |
| 6 | EN1 | Chip Enable of Channel 1 (Active High). $V_{EN1} \leq V_{IN1}$. |
| 7 | VIN1 | Power Input of Channel 1. |
| 8 | LX1 | Pin for Switching of Channel 1. |
| 10 | FB2 | Feedback of Channel 2. |
| 12 | EN2 | Chip Enable of Channel 2 (Active High). $V_{EN2} \leq V_{IN2}$. |



Absolute Maximum Ratings

These are stress ratings only and functional operation is not implied. Exposure to absolute maximum ratings for prolonged time periods may affect device reliability. All voltages are with respect to ground.

| | | | |
|--|----------------------------------|--------------------------------|----------------|
| Input Voltage..... | -0.3V to 6.5V | Junction Temperature..... | 150°C |
| En1, Fb1, Lx1, En2, Fb2 and LX2 Pin Voltage..... | -0.3V to (V _{IN} +0.3V) | Storage Temperature Range..... | -65°C to 150°C |
| | | Soldering Temperature..... | 260°C, 10sec |

Recommended Operating Conditions

| | | | |
|---------------------|--------------|---------------------------------|----------------|
| Supply Voltage..... | 2.5V to 5.5V | Ambient Temperature Range..... | -40°C to 85°C |
| | | Junction Temperature Range..... | -40°C to 125°C |

Thermal Information

| Parameter | Symbol | Package | Maximum | Unit |
|--|----------------|-------------|---------|------|
| Thermal Resistance (Junction to ambient) | θ_{JA} | WDFN 3x3-12 | 60 | °C/W |
| Thermal Resistance (Junction to case) | θ_{JC} | WDFN 3x3-12 | 8.5 | °C/W |
| Power Dissipation | P _D | WDFN 3x3-12 | 1.66 | W |



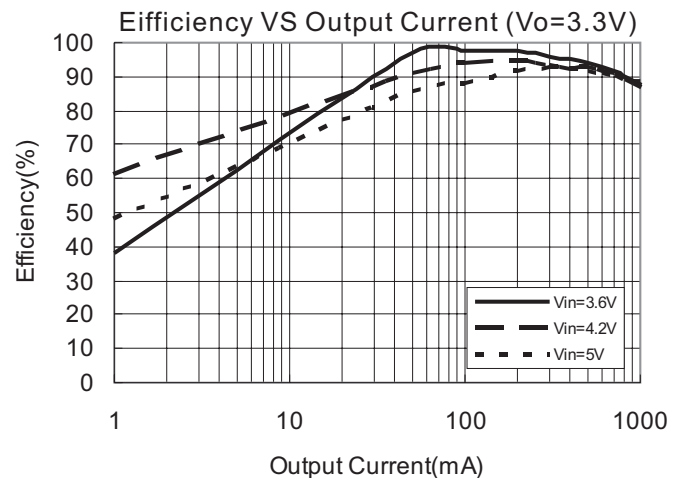
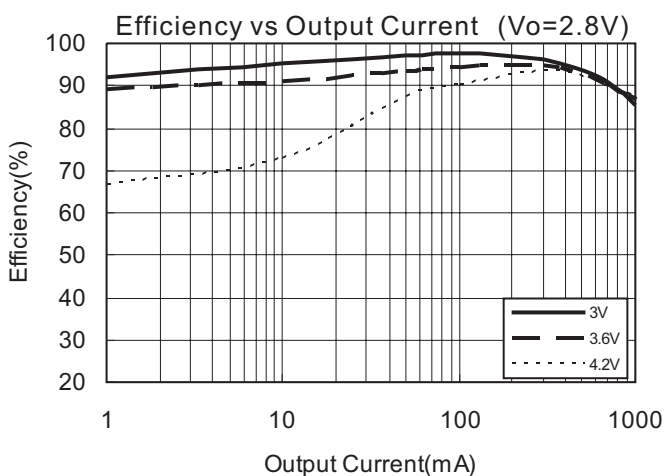
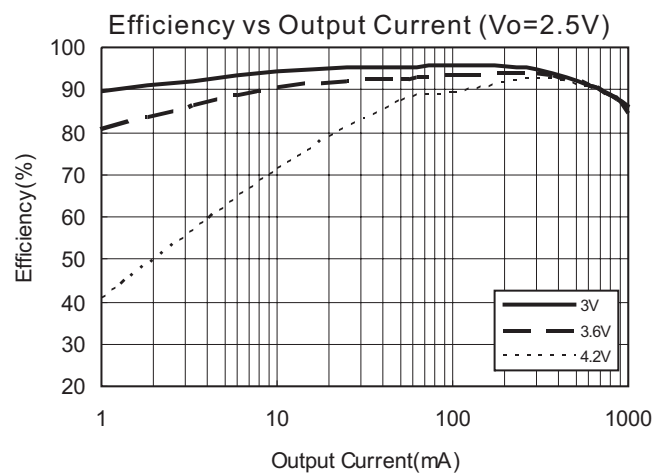
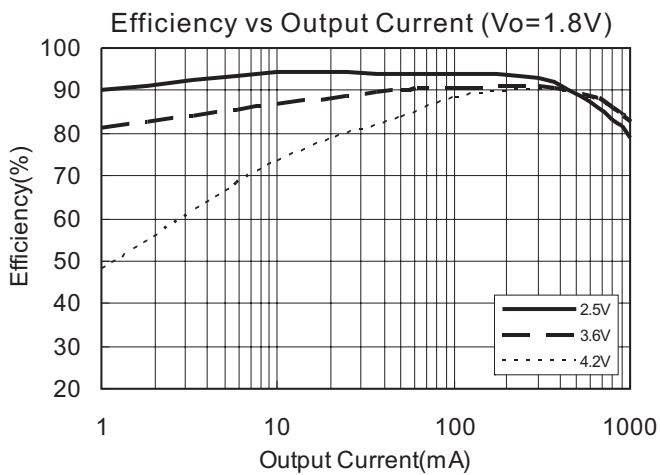
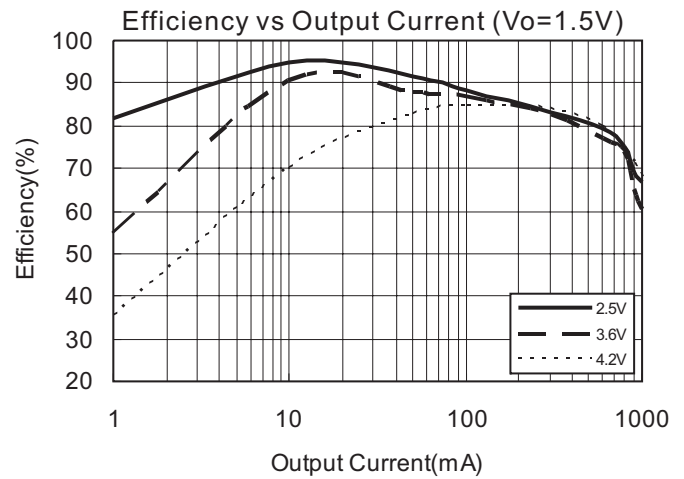
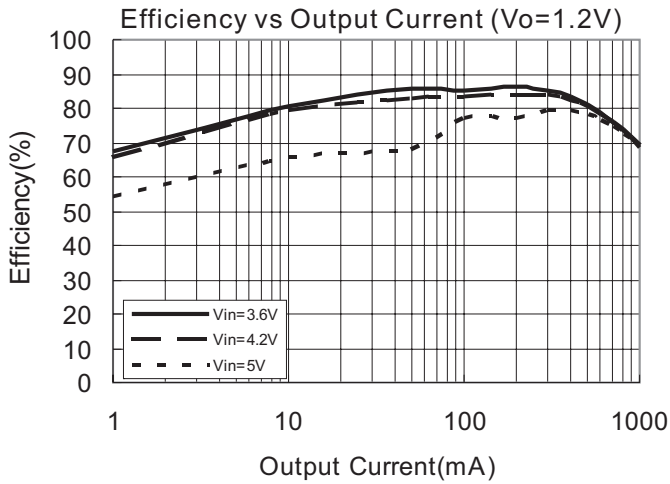
Electrical Characteristic

$T_A=25^{\circ}\text{C}$, $V_{IN}=3.6\text{V}$, $V_O=1.8\text{V}$, $C_{IN}=10\mu\text{F}$, $C_O=10\mu\text{F}$, $L=2.2\mu\text{H}$, unless otherwise noted.

| PARAMETER | SYMBOL | Test Conditions | MIN | TYP | MAX | UNITS |
|-----------------------------------|-----------------|--|----------|------------|-------|--------------------|
| Input Voltage Range | V_{IN} | | 2.5 | | 5.5 | V |
| Regulated Feedback Voltage | V_{FB} | | 0.588 | 0.6 | 0.612 | V |
| Reference Voltage Line Regulation | ΔV_{FB} | | | 0.3 | | %/V |
| Regulated Output Voltage Accuracy | V_O | $I_O = 100\text{mA}$ | -3 | | +3 | % |
| Peak Inductor Current | I_{PK} | $V_{IN}=3\text{V}, V_{FB} = 0.5\text{V}$ or $V_O=90\%$ | | 1.5 | | A |
| Output Voltage Line Regulation | LNR | $V_{IN} = 2.5\text{V to } 5\text{V}, I_O=10\text{mA}$ | | 0.2 | 0.5 | %/V |
| Output Voltage Load Regulation | LDR | $I_O=1\text{mA to } 1\text{A}$ | | 0.5 | 1.5 | % |
| Quiescent Current (per channel) | I_Q | No load | | 40 | 70 | μA |
| Shutdown Current (per channel) | I_{SD} | $V_{EN} = 0\text{V}$ | | 0.1 | 1 | μA |
| Oscillator Frequency | f_{OSC} | $V_O = 100\%$ | 1.2 | 1.5 | 1.8 | MHz |
| | | $V_{FB} = 0\text{V}$ or $V_O = 0\text{V}$ | | 500 | | kHz |
| Drain-Source On-State Resistance | $R_{DS(ON)}$ | $I_{DS}=100\text{mA}$ | P MOSFET | 0.3 | 0.45 | Ω |
| | | | N MOSFET | 0.35 | 0.5 | Ω |
| SW Leakage Current (per channel) | I_{LSW} | | | ± 0.01 | 1 | μA |
| High Efficiency | η | | | 96 | | % |
| EN Threshold High | V_{EH} | | 1.5 | | | V |
| EN Threshold Low | V_{EL} | | | | 0.3 | V |
| EN Leakage Current | I_{EN} | | | ± 0.01 | | μA |
| Over Temperature Protection | OTP | | | 150 | | $^{\circ}\text{C}$ |
| OTP Hysteresis | OTH | | | 30 | | $^{\circ}\text{C}$ |

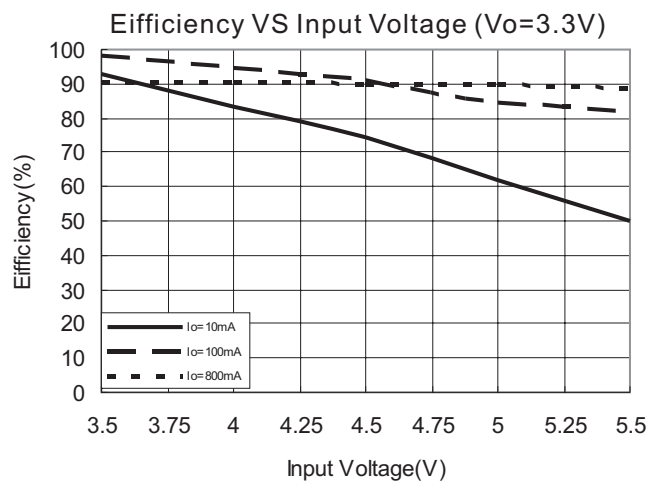
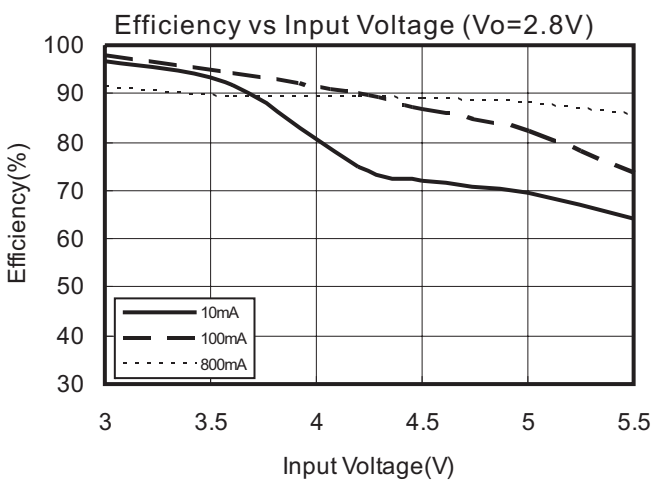
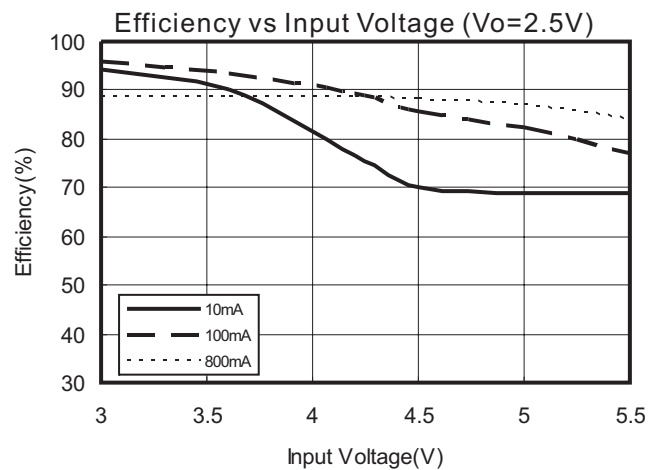
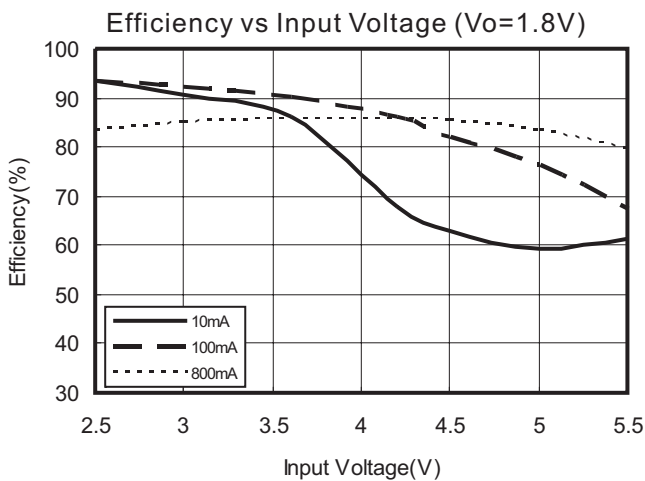
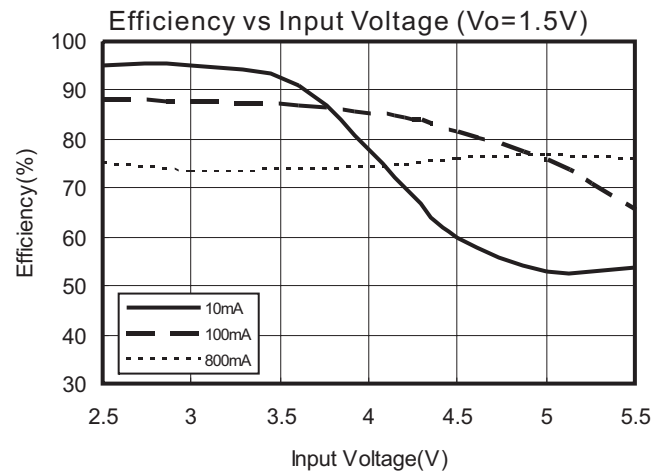
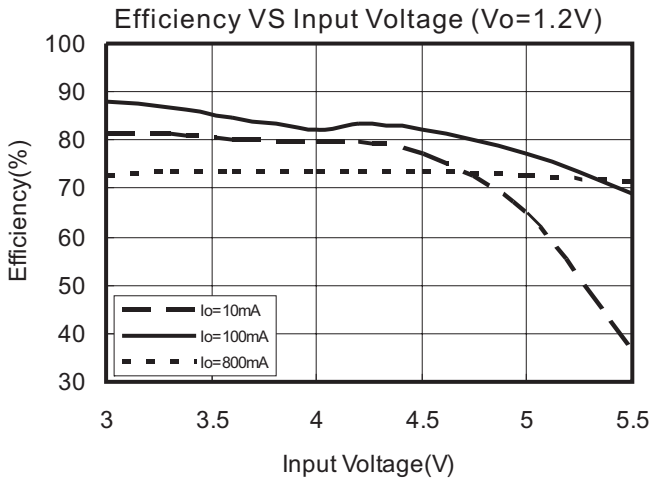
Typical Performance Characteristics

$T_A=25^\circ\text{C}$, $C_{IN}=10\mu\text{F}$, $C_O=10\mu\text{F}$, $L=4.7\mu\text{H}$, unless otherwise noted.



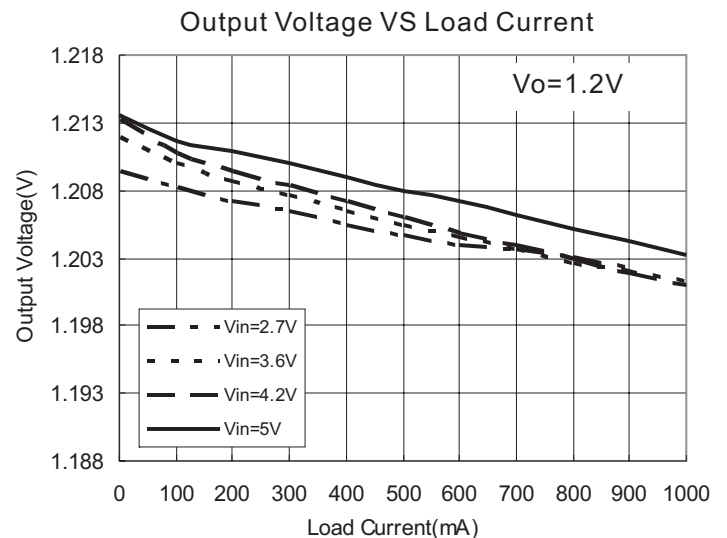
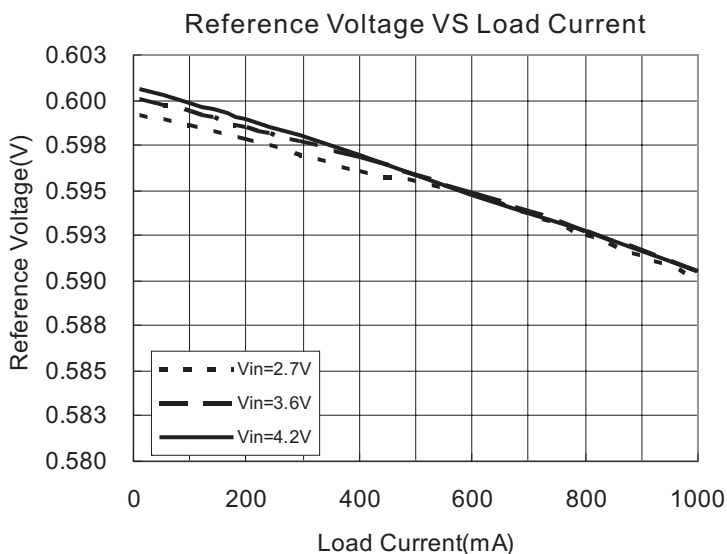
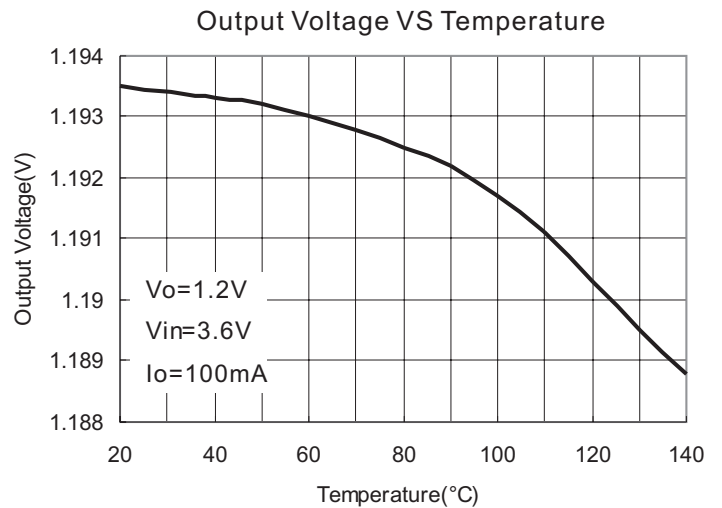
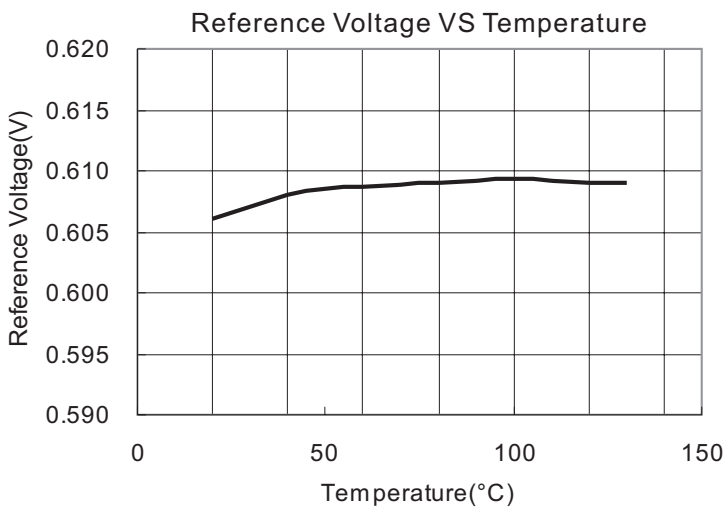
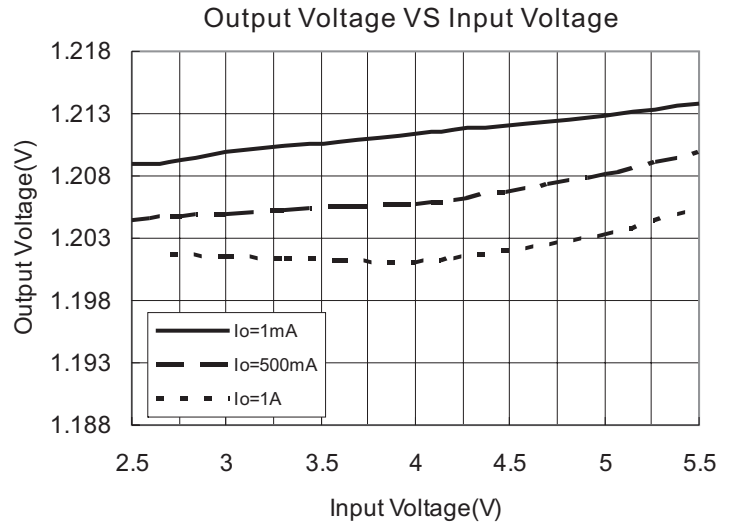
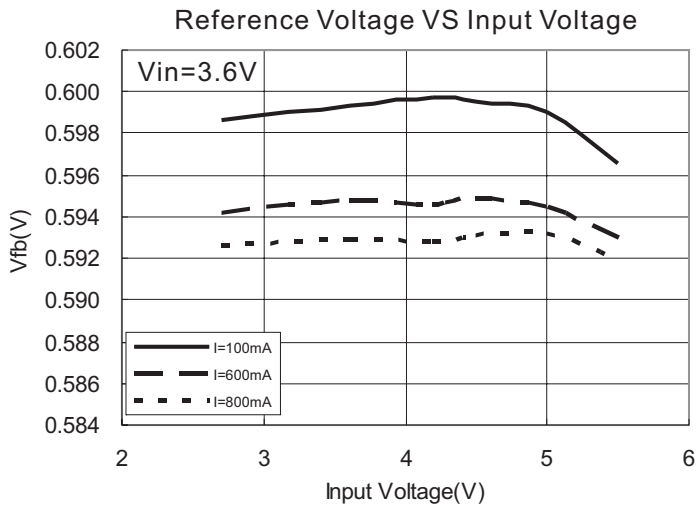
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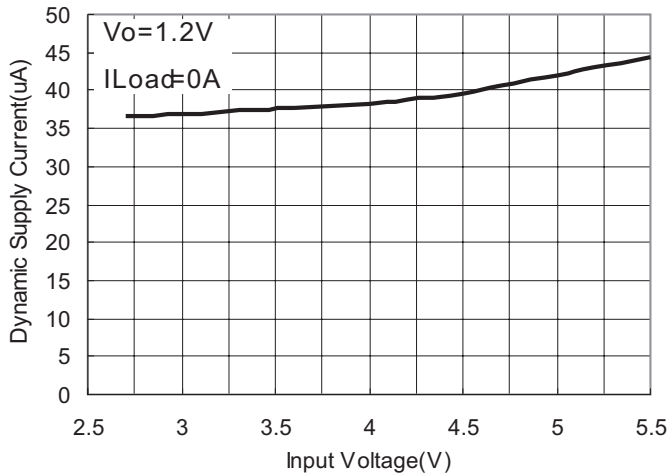
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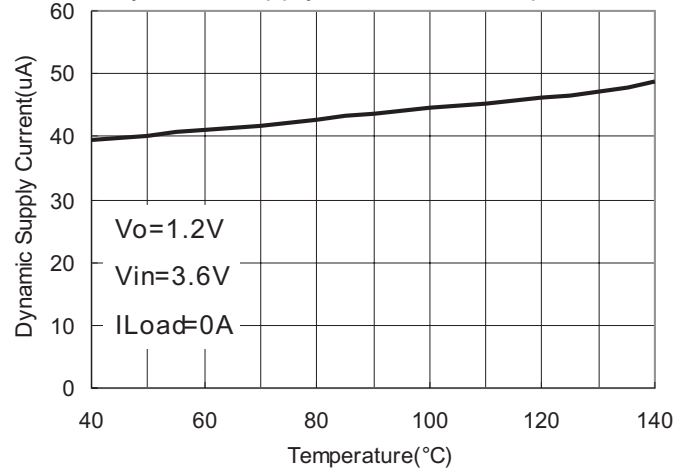
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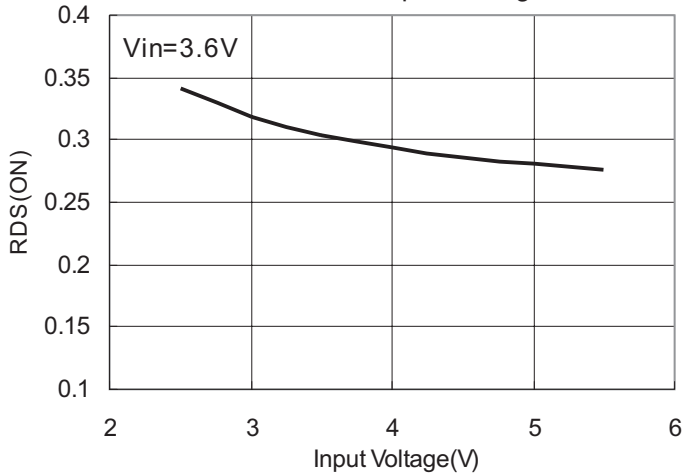
Dynamic Supply Current VS Input Voltage



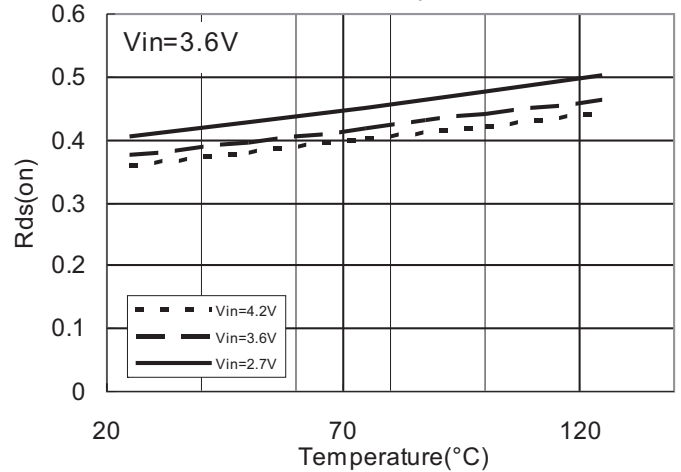
Dynamic Supply Current VS Temperature



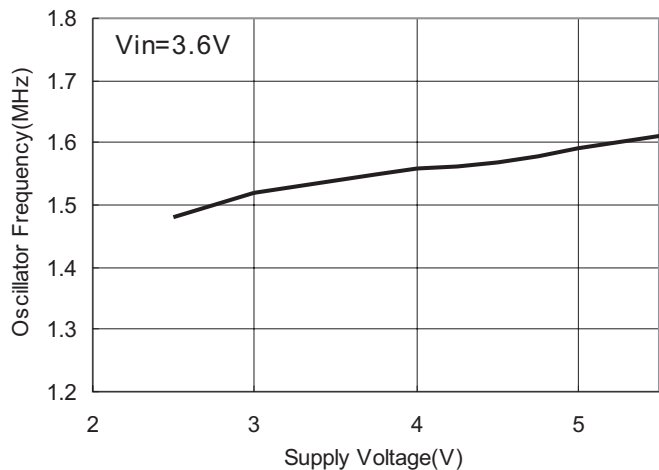
Rdson VS Input Voltage



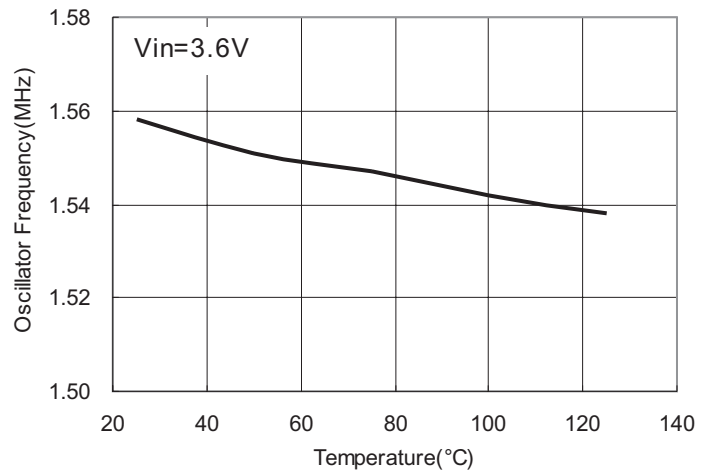
Rdson VS Temperature



Oscillator Frequency VS Supply Voltage



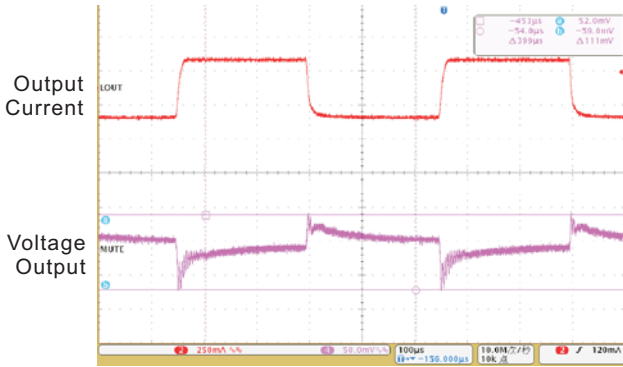
Oscillator Frequency VS Temperature



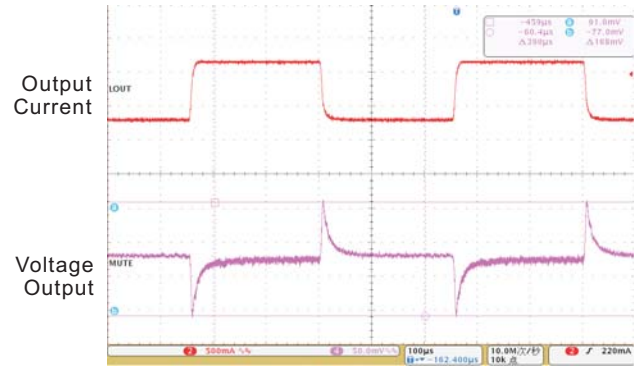
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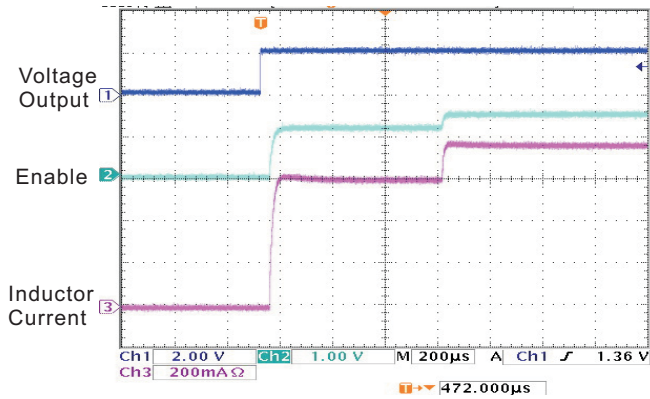
Load Transient
 $I_o=0\text{-}500\text{mA}$ $V_o=3.3\text{V}$ $V_{in}=5\text{V}$



Load Transient
 $I_o=0\text{-}1\text{A}$ $V_o=1.2\text{V}$ $V_{in}=3.6\text{V}$



Start-up from Shutdown
 $V_o=1.8\text{V}$, $V_{in}=3.6\text{V}$



Application Information

The basic PAM2306 application circuit is shown in Page 1. External component selection is determined by the load requirement, selecting L first and then Cin and Cout.

Inductor Selection

For most applications, the value of the inductor will fall in the range of 1μH to 4.7μH. Its value is chosen based on the desired ripple current. Large value inductors lower ripple current and small value inductors result in higher ripple currents. Higher VIN or Vout also increases the ripple current as shown in equation 1. A reasonable starting point for setting ripple current is ΔIL = 400mA (40% of 1A).

$$\Delta I_L = \frac{1}{(f)(L)} V_{OUT} \left(1 - \frac{V_{OUT}}{V_{IN}} \right) \quad (1)$$

The DC current rating of the inductor should be at least equal to the maximum load current plus half the ripple current to prevent core saturation. Thus, a 1.4A rated inductor should be enough for most applications (1A + 400mA). For better efficiency, choose a low DC-resistance inductor.

| | | | | | |
|----|-------|-------|-------|-------|-------|
| Vo | 1.2V | 1.5V | 1.8V | 2.5V | 3.3V |
| L | 2.2μH | 2.2μH | 2.2μH | 4.7μH | 4.7μH |

CIN and COUT Selection

In continuous mode, the source current of the top MOSFET is a square wave of duty cycle Vout/Vin. To prevent large voltage transients, a low ESR input capacitor sized for the maximum RMS current must be used. The maximum RMS capacitor current is given by:

$$C_{IN} \text{ required } I_{RMS} \cong I_{OMAX} \frac{[V_{OUT}(V_{IN} - V_{OUT})]^{1/2}}{V_{IN}}$$

This formula has a maximum at VIN = 2Vout, where IRMS = IOUT/2. This simple worst-case condition is commonly used for design because even significant deviations do not offer much relief. Note that the capacitor manufacturer's ripple current ratings are often based on 2000 hours of life. This makes it advisable to further derate the capacitor, or choose a capacitor rated at a higher temperature than required. Consult the manufacturer if there is any question.

The selection of Cout is driven by the required effective series resistance (ESR).

Typically, once the ESR requirement for Cout has been met, the RMS current rating generally far exceeds the I_{ripple}(P-P) requirement. The output ripple ΔVout is determined by:

$$\Delta V_{OUT} \cong \Delta I_L \left(ESR + \frac{1}{8fC_{OUT}} \right)$$

Where f = operating frequency, C_{OUT} = output capacitance and ΔIL = ripple current in the inductor. For a fixed output voltage, the output ripple is highest at maximum input voltage since ΔIL increases with input voltage.

Using Ceramic Input and Output Capacitors

Higher values, lower cost ceramic capacitors are now becoming available in smaller case sizes. Their high ripple current, high voltage rating and low ESR make them ideal for switching regulator applications. Using ceramic capacitors can achieve very low output ripple and small circuit size.

When choosing the input and output ceramic capacitors, choose the X5R or X7R dielectric formulations. These dielectrics have the best temperature and voltage characteristics of all the ceramics for a given value and size.

Thermal consideration

Thermal protection limits power dissipation in the PAM2306. When the junction temperature exceeds 150°C, the OTP (Over Temperature Protection) starts the thermal shutdown and turns the pass transistor off. The pass transistor resumes operation after the junction temperature drops below 120°C.

For continuous operation, the junction temperature should be maintained below 125°C. The power dissipation is defined as:

$$P_D = I_o^2 \frac{V_o R_{DS(ON)H} + (V_{IN} - V_o) R_{DS(ON)L}}{V_{IN}} + (t_{SW} F_s I_o + I_Q) V_{IN}$$

I_o is the step-down converter quiescent current. The term tsw is used to estimate the full load step-down converter switching losses.

For the condition where the step-down converter is in dropout at 100% duty cycle, the total device dissipation reduces to:

$$P_D = I_O^2 R_{DS(ON)} + I_Q V_{IN}$$

Since $R_{DS(ON)}$, quiescent current, and switching losses all vary with input voltage, the total losses should be investigated over the complete input voltage range. The maximum power dissipation depends on the thermal resistance of IC package, PCB layout, the rate of surrounding airflow and temperature difference between junction and ambient. The maximum power dissipation can be calculated by the following formula:

$$P_D = \frac{T_{J(MAX)} - T_A}{\theta_{JA}}$$

Where $T_J(max)$ is the maximum allowable junction temperature 125°C. T_A is the ambient temperature and θ_{JA} is the thermal resistance from the junction to the ambient. Based on the standard JEDEC for a two layers thermal test board, the thermal resistance θ_{JA} of DFN3X3 is 60°C/W. The maximum power dissipation at $T_A = 25^\circ\text{C}$ can be calculated by following formula:

$$P_D = (125^\circ\text{C} - 25^\circ\text{C}) / 60^\circ\text{C/W} = 1.66\text{W}$$

Setting the Output Voltage

The internal reference is 0.6V (Typical). The output voltage is calculated as below:

$$V_O = 0.6 \times \left(1 + \frac{R1}{R2} \right)$$

The output voltage is given by Table 1.

Table 1: Resistor selection for output voltage setting

| Vo | R1 | R2 |
|------|------|------|
| 1.2V | 100k | 100k |
| 1.5V | 150k | 100k |
| 1.8V | 200k | 100k |
| 2.5V | 380k | 120k |
| 3.3V | 540k | 120k |

100% Duty Cycle Operation

As the input voltage approaches the output voltage, the converter turns the P-channel transistor continuously on. In this mode the output voltage is equal to the input voltage minus the voltage drop across the P - channel transistor:

$$V_{OUT} = V_{IN} - I_{LOAD} (R_{dson} + R_L)$$

where R_{dson} = P-channel switch ON resistance, I_{LOAD} = Output current, R_L = Inductor DC resistance

UVLO and Soft-Start

The reference and the circuit remain reset until the VIN crosses its UVLO threshold.

The PAM2306 has an internal soft-start circuit that limits the in-rush current during start-up. This prevents possible voltage drops of the input voltage and eliminates the output voltage overshoot. The soft-start acts as a digital circuit to increase the switch current in several steps to the P-channel current limit (1500mA).

Short Circuit Protection

The switch peak current is limited cycle-by-cycle to a typical value of 1500mA. In the event of an output voltage short circuit, the device operates with a frequency of 400kHz and minimum duty cycle, therefore the average input current is typically 200mA.

Thermal Shutdown

When the die temperature exceeds 150°C, a reset occurs and the reset remains until the temperature decrease to 120°C, at which time the circuit can be restarted.

PCB Layout Check List

When laying out the printed circuit board, the following checklist should be used to ensure proper operation of the PAM2306. These items are also illustrated graphically in Figure 1. Check the following in your layout:

1. The power traces, consisting of the GND trace, the SW trace and the VIN trace should be kept short, direct and wide.
2. Does the FB pin connect directly to the feedback resistors? The resistive divider R1/R2 must be connected between the (+) plate of C_{OUT} and ground.
3. Does the (+) plate of C_{IN} connect to VIN as closely as possible? This capacitor provides the AC current to the internal power MOSFETs.
4. Keep the switching node, SW, away from the sensitive FB node.
5. Keep the (-) plates of C_{IN} and C_{OUT} as close as possible.

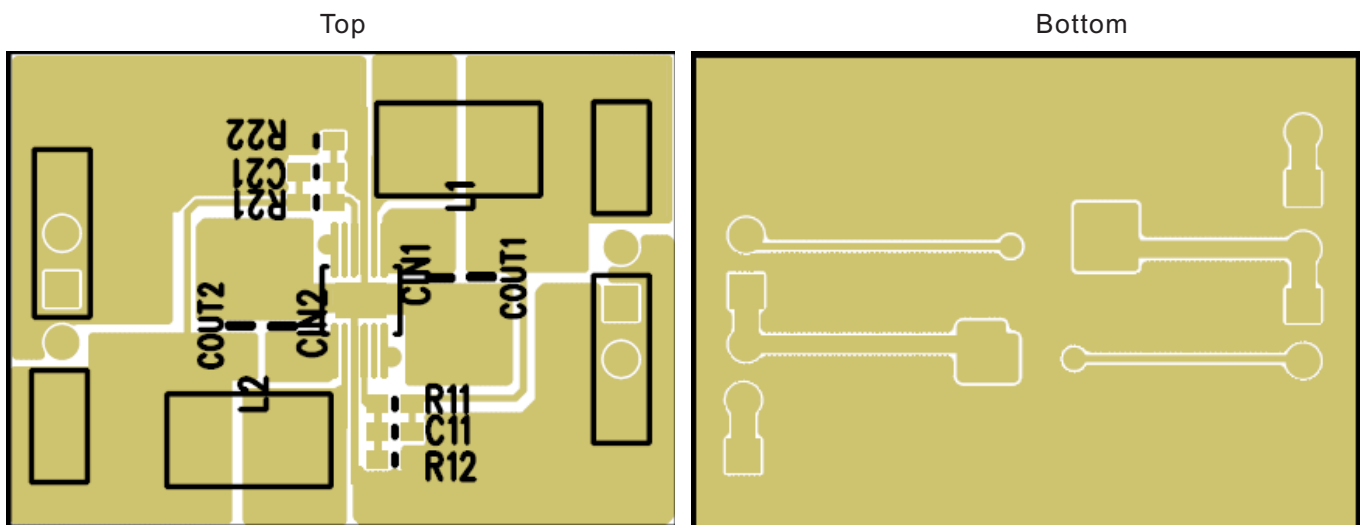
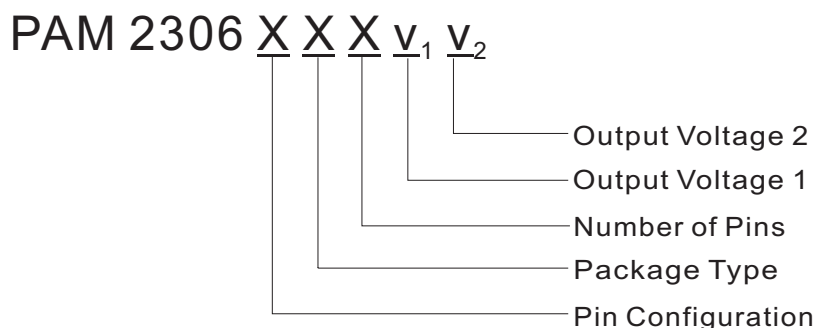


Figure 1 :PAM2306 Suggested Layout

Ordering Information

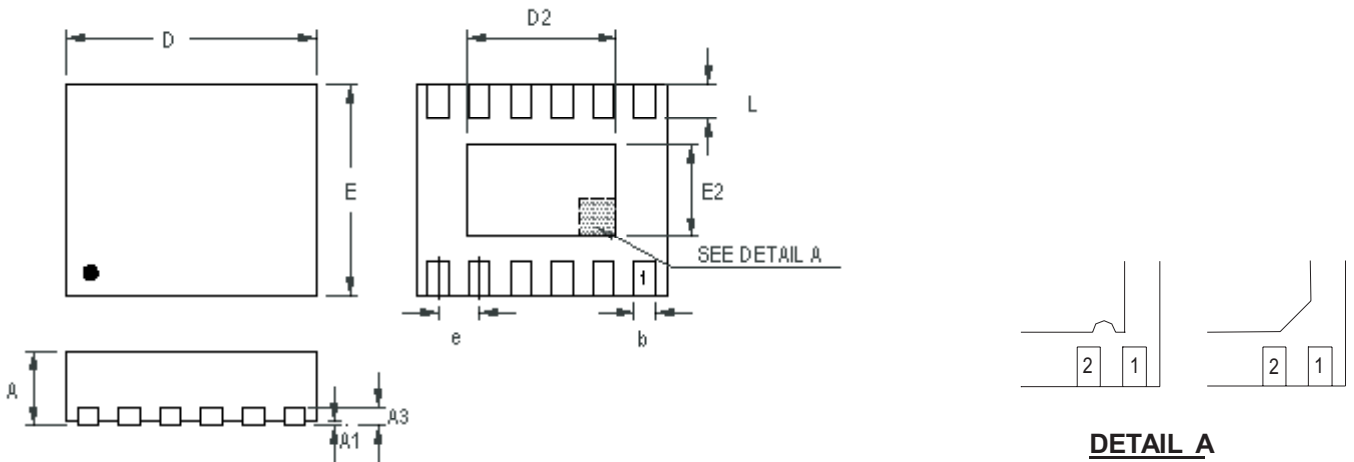


| Pin Configuration | Package Type | Number of Pins | Output Voltage | |
|---|--------------|----------------|--|--|
| | | | v ₁ | v ₂ |
| A Type 1. VIN2 2. LX2 3. GND 4. FB1 5. NC1 6. EN1 7. VIN1 8. LX1 9. GND 10. FB2 11: NC2 12 :EN2 | Y: WDFN 3x3 | P: 12 | K: 3.3V H: 2.8V G: 2.5V E: 1.8V C: 1.5V B: 1.2V A: Adj | K: 3.3V H: 2.8V G: 2.5V E: 1.8V C: 1.5V B: 1.2V A: Adj |

| Part Number | Marking | Package Type | Standard Package |
|---|--|--------------|-----------------------|
| PAM2306AYPv ₁ v ₂ | 2306v ₁ v ₂ XXXYW | WDFN3x3-12 | 3,000 Units/Tape&Reel |

Outline Dimensions

3x3 mm WDFN 12



DETAIL A

Pin #1 ID and Tie Bar Mark Options

Note : The configuration of the Pin #1 identifier is optional, but must be located within the zone indicated.

| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min | Max | Min | Max |
| A | 0.700 | 0.800 | 0.028 | 0.031 |
| A1 | 0.000 | 0.050 | 0.000 | 0.002 |
| A3 | 0.175 | 0.250 | 0.007 | 0.010 |
| b | 0.150 | 0.250 | 0.006 | 0.010 |
| D | 2.950 | 3.050 | 0.116 | 0.120 |
| D2 | 2.300 | 2.650 | 0.091 | 0.104 |
| E | 2.950 | 3.050 | 0.116 | 0.120 |
| E2 | 1.400 | 1.750 | 0.055 | 0.069 |
| e | 0.450 | | 0.018 | |
| L | 0.350 | 0.450 | 0.014 | 0.018 |